**Analog Power** AMD534C

# P & N-Channel 30-V (D-S) MOSFET

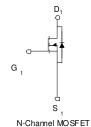
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

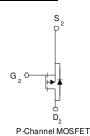
•	Low $r_{DS(on)}$ provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY						
$V_{DS}(V)$	$r_{DS(on)} m(\Omega)$	I <sub>D</sub> (A)				
20	$39 @ V_{CS} = 4.5V$	30				
30	$29 @ V_{GS} = 10V$	36				
20	29 @ V <sub>CS</sub> = -4.5V	-36				
-30	22 @ V <sub>CS</sub> =-10V	39				







COMPLIANT	5
HALOGEN	
FREE	
$C_{\rm A} = 25^{\circ}{\rm C}$	71

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED)							
Parameter Parameter			N-Channel	P-Channel	Units		
Drain-Source Voltage		$V_{DS}$	30	-30	V		
Gate-Source Voltage	Van 5000004	$V_{CS}$	±20	±20	V		
	T <sub>A</sub> =25°C	т	36	-39	A		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70°C	I <sub>D</sub>	30	-32			
Pulsed Drain Current <sup>b</sup>			40	-40			
Continuous Source Current (Diode Conduction) <sup>a</sup>			30	-30	Α		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	$P_{\mathrm{D}}$	50	50	W		
Operating Junction and Storage Temperature Range			-55 to	°C			

THERMAL RESISTANCE RATINGS						
Parameter Symbol Maximum Units						
Maximum Junction-to-Ambient <sup>a</sup>	$R_{ heta JA}$	50	°C/W			
Maximum Junction-to-Case	$R_{ heta JC}$	3.0	°C/W			

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### Notes

- Surface Mounted on 1" x 1" FR4 Board. a.
- Pulse width limited by maximum junction temperature b.

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SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)								
Demonstra	G .I.I	T ( C 194	Limits				TT	
Parameter	Symbol	Test Conditions	Ch	Min	Тур	Max	Unit	
Static								
Cata Thursdayld Valtage	17	$V_{CS} = V_{DS}$ , $I_D = 250 \text{ uA}$	N	0.6			V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{OS} = V_{DS}$ , $I_{D} = -250 \text{ uA}$	P	-0.6			ľ	
Gate-Body Leakage	I <sub>CSS</sub>	$V_{OS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$	P			±100	пA	
Care Body Bandy	-(05)	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	N			±100	11/-1	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	P N			-1 1	uА	
	+ -	$V_{DS} = 24 \text{ V}, V_{CS} = 0 \text{ V}$ $V_{DS} = 5 \text{ V}, V_{CS} = 10 \text{ V}$	N	20		1		
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	P	-20			Α	
		VOS = 10  V, ID = 6.9  A	N			29		
Drain-Source On-Resistance <sup>a</sup>	$r_{DS(on)}$	$VCS=4.5 \text{ V}, I_D=6 \text{ A}$	14			39	mΩ	
Brain source on rusistance	*135(GII)	VGS=-10 V, I <sub>D</sub> =-5.2 A	P			22 29		
	_	VCS=-4.5  V, ID = -4.2  A $V_{DS}=15 \text{ V, I}_{D}=6.9 \text{ A}$	N		25	29		
Forward Tranconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_D = 0.9 \text{ A}$ $V_{DS} = -15 \text{ V}, I_D = -5.2 \text{ A}$	P		10		S	
Dynamic		.р. 10 1, гр 1, г. г.						
			N		6.0			
Total Gate Charge	Q	N-Channel	P		10		пС	
Gate-Source Charge	$Q_{2s}$	$V_{DS}=15V$ , $V_{CS}=10V$ , $I_{D}=6.9A$	N		1.0			
Cate-Source Charge	<b>Q</b> gs	P-Channel	P		2.4			
Gate-Drain Charge	$Q_{gd}$	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.2A	N		1.5			
Cite-Dain Grage	<b>Q</b> gu		P		3.9			
Turn-On Delay Time	td(on)	N-Chaneel	N		7.4			
Tuni-Grizzay Tine	ta(on)		P		7.6			
Rise Time	tr	$V_{DD}=15V, V_{CS}=10V, I_{D}=1A$	N		4			
-	-	R <sub>cen</sub> =6Ω, P-Channel	P N	$\vdash$	6.8		nS	
Turn-Off Delay Time	td(off)	P-Channel Vbb=15V, Vos=10V, Ib=1A	P		33.6			
-		VDD=13V, VGS=10V, ID=1A RGFN=6Ω	N	<del>                                     </del>	3.6		1	
Fall-Time	<b>t</b> f	KGEN=US 2	P	<del>                                     </del>	23.2			

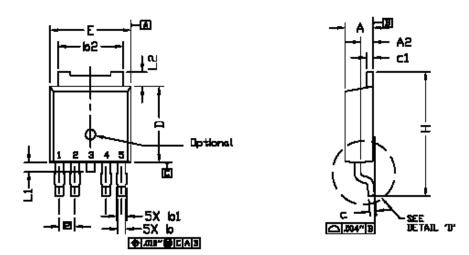
#### Notes

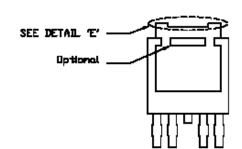
- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

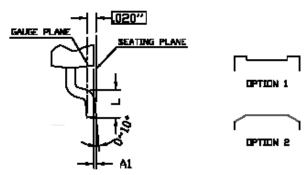
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## TO252\_4L PACKAGE OUTLINE







DETAIL 'D'
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DETAIL 'E'

8 Y M	DIMENS	ION IN MILLI	METERS	DIMENSIONS IN INCHES		
B O L	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	2.184	2.286	2.388	0.086	0.090	0.094
A1	0.000	_	0.127	0.000	_	0.005
A2	0.889	_	1.143	0.035	_	0.045
b	0.508	_	0.711	0.020	_	0.028
b1	0.584	_	0.787	0.023	_	0.031
b2	4.953	_	5.461	0.195	_	0.215
c	0.457	0.508	0.610	0.018	0.020	0.024
c1	0.457	_	0.610	0.018	_	0.024
D	5.969	6.096	6.223	0.235	0.240	0.245
E	6.350	6.604	6.731	0.250	0.260	0.265
8	1.270 BSC. 0.050 BSC.					
Н	9.398	_	10.414	0.370	_	0.410
L	1.270	_	2.032	0.050	_	0.080
L1	_	_	1.016	<b>—</b>		0.040
12	0.889		1,270	0.035		0.050

#### NOTE

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH SHOULD BE LESS THAN 6 MIL.
  2. DIMENSION L IS MEASURED IN GAUGE PLANE.
  3. TOLERANCE 0.10 mm UNLESS OTHERWISE SPECIFIED.

- 4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
- 5, REFER TO JEDEC TO-252 (AD).